

**IN THE CLAIMS**

Please amend the claims as follows:

Claim 1 (currently amended): A method of manufacturing a semiconductor device, comprising ~~the steps of~~:

- (a) forming a first interlayer insulation film on a semiconductor substrate;
- (b) depositing sequentially and patterning a predetermined first metal film on said first interlayer insulation film; [[and]]
- (c) depositing an antireflection film including a dielectric layer on a semiconductor substrate an upper surface of said first metal film to form a lower electrode having said antireflection film on its upper surface;
- (d) patterning said first metal film and said antireflection film to form a lower electrode having said antireflection film on an upper surface thereof; [[(b)]]
- (e) forming [[an]] a second interlayer insulation film on said lower electrode antireflection film; [[and]]
- (f) forming first and second openings respectively in a capacitor element forming first region [[of]] and in a contact forming second region [[of]] in said second interlayer insulation film, respectively on said lower electrode; [[(c)]]
- (g) removing a portion of said antireflection film [[in]] where said second opening is formed; and (d)
- (h) depositing a predetermined second metal film on said second interlayer insulation film; having said first and second openings and
- (i) removing said second metal film other than said second metal film except in said first and second openings[[,]] to form an upper electrode of said capacitor element in said first opening, and a contact in said second opening.

Claim 2 (currently amended): The method of manufacturing a semiconductor device according to claim 1, further comprising ~~the step of:~~ [[e)]]

(j) depositing and patterning a predetermined third metal film on said second interlayer insulation film; and

(k) patterning said third metal film to form an interconnect line which is including a first portion and a second portion, said first and second portions of the interconnect line being individually connected to said contact and said upper electrode, respectively,

wherein said ~~step (e) being~~ steps (j) and (k) are performed after said step [[d)]] (i).